	Hits	Search Text	DB	Time stamp
Number				_
1	121	<pre>(no or (nitric with oxide)) and cvd and (nitrogen with dop\$3 with oxide) and (thermal adj oxidation)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/08
2	108	((no or (nitric with oxide)) and cvd and (nitrogen with dop\$3 with oxide) and (thermal adj oxidation)) and	USPAT; US-PGPUB; EPO; JPO;	2004/01/08
3	100	(@ad<20011012 or @rlad<20011012) ("no".u/c. or (nitric with oxide)) and cvd and (nitrogen with dop\$3 with oxide) and (thermal adj oxidation)	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/01/08
4	93	(("no".u/c. or (nitric with oxide)) and cvd and (nitrogen with dop\$3 with oxide) and (thermal adj oxidation)) and	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/01/08
5	88	(@ad<20011012 or @rlad<20011012) ("no".u/c. or (nitric with oxide)) and cvd and {(thermal adj oxidation) same (thermal adj nitridation))	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/08
6	85	(("no".u/c. or (nitric with oxide)) and cvd and ((thermal adj oxidation) same (thermal adj nitridation))) and	USPAT; US-PGPUB; EPO; JPO;	2004/01/08 18:32
7	2	(@ad<20011012 or @rlad<20011012) ("no".u/c. or (nitric with oxide)) and cvd and ((thermal adj oxidation) same (thermal adj nitridation) same (gate adj oxide))	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/08 18:32
8	31	("no".u/c. or (nitric with oxide)) and cvd and ((thermal adj oxidation) same (gate adj oxide)) and (thermal adj nitridation)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/08 18:32
9	30	(("no".u/c. or (nitric with oxide)) and cvd and ((thermal adj oxidation) same (gate adj oxide)) and (thermal adj nitridation)) and (@ad<20011012 or @rlad<20011012)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/01/08 18:32
-	355	(gate with oxide) and (oxidiz\$3 with substrate) and (nitrid\$5 with (no or (nitric with oxide))) and cvd	USPAT; EPO; JPO; DERWENT	2004/01/08 15:52
-	197	((gate with oxide) and (oxidiz\$3 with substrate) and (nitrid\$5 with (no or (nitric with oxide))) and cvd) and temperature and (atm or atmosphere or	USPAT; EPO; JPO; DERWENT	2002/07/30 14:02
-	149	torr) (((gate with oxide) and (oxidiz\$3 with substrate) and (nitrid\$5 with (no or (nitric with oxide))) and cvd) and temperature and (atm or atmosphere or torr)) and 438/\$3.ccls.	USPAT; EPO; JPO; DERWENT	2002/07/30 14:02
-	119	((((gate with oxide) and (oxidiz\$3 with substrate) and (nitrid\$5 with (no or (nitric with oxide))) and cvd) and temperature and (atm or atmosphere or torr)) and 438/\$3.ccls.) and (gate with electrode)	USPAT; EPO; JPO; DERWENT	2002/07/30
-	145	(gate with oxide) same (oxidiz\$3 with substrate) and (nitrid\$5 with (no or (nitric with oxide))) and cvd	USPAT; EPO; JPO; DERWENT	2002/07/31
-	76	((gate with oxide)) same (oxidiz\$3 with substrate) and (nitrid\$5 with (no or (nitric with oxide))) and cvd) and temperature and (atm or atmosphere or torr)	USPAT; EPO; JPO; DERWENT	2002/07/30 14:02
-	59	(((gate with oxide) same (oxidiz\$3 with substrate) and (nitrid\$5 with (no or (nitric with oxide))) and cvd) and temperature and (atm or atmosphere or torr)) and 438/\$3.ccls.	USPAT; EPO; JPO; DERWENT	2002/07/30 14:02

-	5	(gate with oxide) same (oxidiz\$3 with	USPAT;	2002/07/30
		substrate) and ((nitrid\$5 with (no or	EPO; JPO;	15:11
	1	(nitric with oxide)) same boron)) and cvd	DERWENT	
l	17	"5650344"	USPAT;	2002/07/30
	1	3030311	EPO; JPO;	15:11
	1		1	15:11
	i '		DERWENT	
-	14	"5403786"	USPAT;	2002/07/31
]	1		EPO; JPO;	14:16
			DERWENT	1
_	26	(gate with oxide) same (oxidiz\$3 with	USPAT;	2002/07/31
	20			1
		substrate) and (nitrid\$5 with (no or	EPO; JPO;	15:57
	\	(nitric with oxide))) and cvd and ono and	DERWENT	
	1	(gate adj electrode)	ļ	ļ
-	22	(gate with oxide) same (oxidiz\$3 with	USPAT;	2002/07/31
	1	substrate) and (nitrid\$5 with (no or	EPO; JPO;	16:33
1	j	(nitric with oxide))) and cvd and ono and	DERWENT	13.33
			DEKWENI	1
	1	((gate adj electrode) with (silicon or		
		polysilicon))		
-	11	((gate with oxide) same (oxidiz\$3 with	USPAT;	2002/07/31
		substrate) and (nitrid\$5 with (no or	EPO; JPO;	15:58
	ļ	(nitric with oxide))) and cvd and one and	DERWENT	
	1	((gate adj electrode) with (silicon or	2011,0011	1
1	1		Į	[
1	1	polysilicon))) and tungsten		
-] 3	(gate with oxide) same (oxidiz\$3 with	USPAT;	2002/07/31
		substrate) and (nitrid\$5 with (no or	EPO; JPO;	16:56
	1	(nitric with oxide))) and cvd and one and	DERWENT	
		(((gate adj electrode) with polycide)		1
1	1	same tungsten)		1
ļ	1		l	0000 (00 (00
-	17	"5650344"	USPAT;	2002/07/31
1			EPO; JPO;	16:56
	1		DERWENT	1
_	3554	(nitrid\$5 with gate with oxide) and cvd	USPAT:	2003/01/13
1	3334	(EPO; JPO;	12:32
				12.32
1	_	// 10 1145 141 / 111	DERWENT	1 2 2 2 4 2 4 2 5 2
-	0	((nitrid\$5 with gate with oxide) same	USPAT;	2003/01/13
	1	(nitirc adj oxide)) and cvd	EPO; JPO;	12:33
			DERWENT	\
-	5	((nitrid\$5 with gate with oxide) same	USPAT;	2003/01/13
	1	(nitric adj oxide)) and cvd	EPO; JPO;	12:33
Ì	}	(HILLIC adj Oxide), and CVd		12.33
		(/ '- '105 '11	DERWENT	0000 (01 (10
-	6	, , ,	USPAT;	2003/01/13
	{	(nitric adj oxide)) and cvd	US-PGPUB;	14:55
			EPO; JPO;	1
	1		DERWENT	1
1 -	0	11040681.URPN.	USPAT	2003/01/13
	1	11010001.01111	JOEAL	14:46
1	1	5724007 mm	110535	1 1111111
_	1 2	5726087.pn.	USPAT;	2003/01/13
1	1		US-PGPUB;	16:28
1	1		EPO; JPO;	1
[1		DERWENT	1
_	355	dry adj oxide	USPAT;	2003/01/13
1		· <u> </u>	US-PGPUB;	16:49
1	1			10.75
•			EPO; JPO;	
	1		DERWENT	
-	518	(gate adj oxide) with angstrom with ("10"	USPAT;	2003/01/13
1	[or "15" or "20")	US-PGPUB;	16:51
}	1		EPO; JPO;	
	1		DERWENT	1
1_	341	(gate adj oxide) with angstrom with ("10"		2003/01/12
	1 241		USPAT;	2003/01/13
]]	or "15")	US-PGPUB;	17:23
	[EPO; JPO;	1
1]		DERWENT	
-	234	((gate adj oxide) with angstrom with	USPAT;	2003/01/13
	'	("10" or "15")) and nitrid\$5	US-PGPUB;	17:06
1	\	,	EPO; JPO;	1
]	[(
		(/	DERWENT	0000 (00 (00
-	46	((gate adj oxide) with angstrom with	USPAT;	2003/01/13
	j	("10" or "15")) same nitrid\$5	US-PGPUB;	17:06
1			EPO; JPO;	Í
				l
	[DERWENT	

- 8	(gate adj oxide) with angstrom with ("10"	USPAT;	2003/01/13
	or "15") with (ultra near2 thin)	US-PGPUB;	17:24
i		EPO; JPO;	,
<u> </u>		DERWENT	